Product data sheet

1. General description

Silicon Carbide Schottky diode in a SOD59A (TO-220AC) plastic package, designed for high frequency switched-mode power supplies.

2. Features and benefits

- · Highly stable switching performance
- · High forward surge capability IFSM
- · Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage			-	-	650	V
I _{F(AV)}	average forward current	$δ = 0.5$; $T_{mb} \le 76$ °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		-	-	20	A
Tj	junction temperature			-	-	175	°C
Static charac	teristics						
V _F	forward voltage	I _F = 20 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.5	1.7	V
		I _F = 20 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.8	2.1	V
Dynamic cha	Dynamic characteristics						
Q _r	recovered charge	I _F = 20 A; dI _F /dt = 500 A/µs; V _R = 400 V; T _j = 25 °C; <u>Fig. 6</u>		-	28	-	nC

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	А	anode		001aaa020
mb	mb	mounting base; connected to cathode	TO-220AC (SOD59A)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
NXPSC20650	TO-220AC	Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59A			

7. Marking

Table 4. Marking codes

Type number	Marking code
NXPSC20650	NXPSC20650

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	650	V
V_{RWM}	crest working reverse voltage		-	650	V
V_R	reverse voltage	DC	-	650	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 76 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	20	Α
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; $T_{mb} \le 76$ °C; squarewave pulse	-	40	Α
I _{FSM}	non-repetitive peak	t _p = 10 ms; T _{j(init)} = 25 °C; SIN	-	100	Α
	forward current	t _p = 10 μs; T _{j(init)} = 25 °C; SIN	-	900	А
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-	175	°C

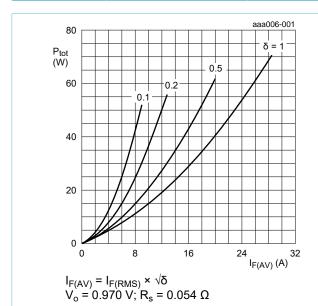


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

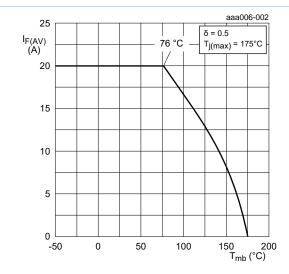
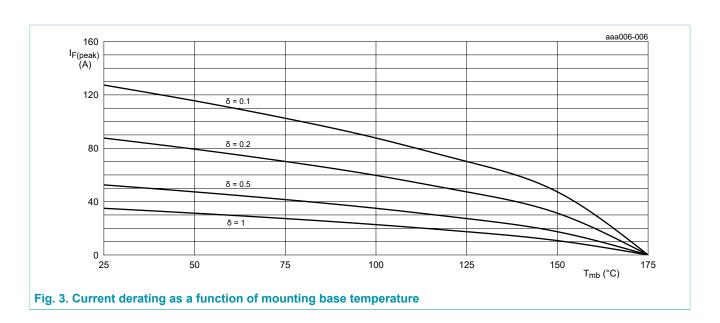


Fig. 2. Forward current as a function of mounting base temperature; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	-	1.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

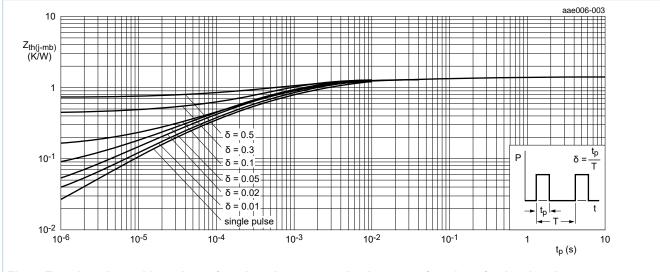


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

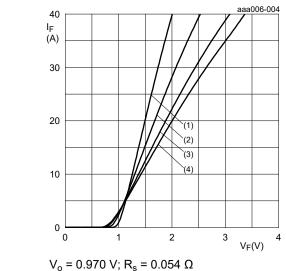
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Mi	п Тур	Max	Unit		
Static char	Static characteristics							
V _F	forward voltage	I _F = 20 A; T _j = 25 °C; <u>Fig. 5</u>	-	1.5	1.7	V		
		I _F = 20 A; T _j = 150 °C; <u>Fig. 5</u>	-	1.8	2.1	V		
I _R	reverse current	V _R = 650 V; T _j = 25 °C	-	-	500	μΑ		
		V _R = 650 V; T _j = 150 °C	-	-	1600	μΑ		
Dynamic cl	haracteristics							
Q _r	recovered charge	$I_F = 20 \text{ A; } dI_F/dt = 500 \text{ A/}\mu\text{s;}$ $V_R = 400 \text{ V; } T_j = 25 \text{ °C; } Fig. 6$	-	28	-	nC		
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C	-	600	-	pF		
		f = 1 MHz; V _R = 300 V; T _j = 25 °C	-	64	-	pF		
		f = 1 MHz; V _R = 600 V; T _j = 25 °C	-	50	-	pF		



(1) $T_j = 25$ °C; typical values (2) $T_j = 100$ °C; typical values (3) $T_j = 150$ °C; typical values (4) $T_j = 175$ °C; typical values

Fig. 5. Forward current as a function of forward voltage; typical values

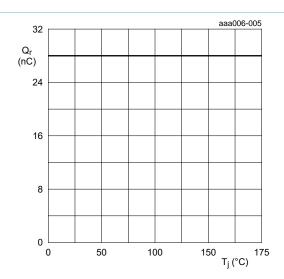
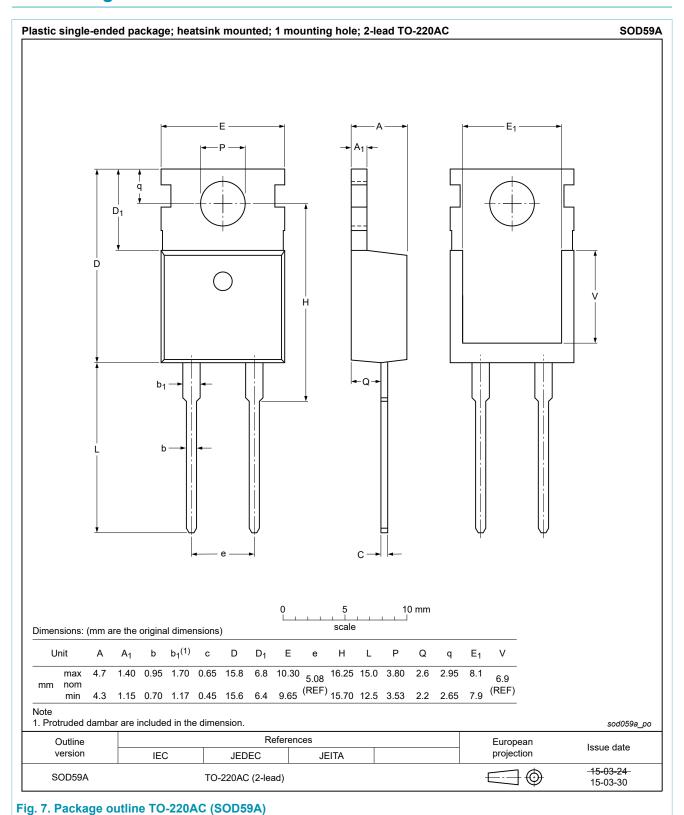


Fig. 6. Recovered charge as a function of junction temperature

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11. Package outline



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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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